

Abstract

In a film-forming apparatus for forming a thin film (15) on a substrate (6) by supplying a gas (13) through a gas nozzle (14) into a vacuum chamber (1) and transforming the gas (13) into a plasma by applying a current to a high-frequency antenna (7), a ceramic inner cylinder (20) is arranged so as to contact with the vacuum chamber (1) at only a small area of the cylinder for preventing adhesion of the film-forming component onto the inner wall of the vacuum chamber (1). In this film-forming apparatus, it is possible to suppress generation of particles and to reduce the workload of the cleaning process.